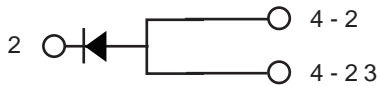


Trench MOS Barrier Schottky Rectifier

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Features

- Advanced trench technology
- Low forward voltage drop
- Low power losses
- High efficiency operation
- Lead Free Finish, RoHS Compliant

Applications

- DC/DC Converters
- AC/DC Adaptors
- Switching Power Supplies
- Freewheeling Diodes

Maximum ratings and electrical characteristics (T_J = 25°C unless otherwise noted)

Parameter		Symbol	Limit		Unit
Maximum repetitive peak reverse voltage		VRRM	120		V
Maximum average forward rectified current		IF(AV)			A
Peak forward surge current 8.3 ms single half sine- wave superimposed on rated load per diode		IFSM	80		A
Operating junction and storage temperature range		TJ, TSTG	-5 to +150		°C
Typical thermal resistance per leg	TO-252	RθJC	6		°C/W
Instantaneous forward voltage per diode			TYP.	MAX.	V
	IF= A	TJ=25°C	0.	0.	
	IF= A	TJ=125°C	0.	-	
	IF=10A	TJ=25°C			
Instantaneous reverse current per diode at rated reverse voltage	TJ=25°C		20		uA
	TJ=125°C		-	50	mA

Notes:

(1) Pulse test: 300 μs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width 0 40 ms

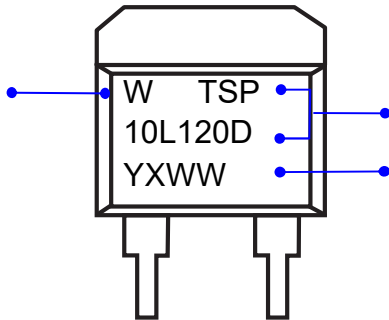
RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)

Percent of Rated Peak Reverse Voltage (%)

PACKAGE OUTLINE DIMENSIONS

Note:unit In(mm)

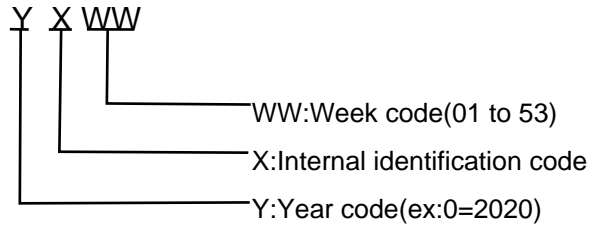
0 D U N L Q J , Q I R U P D W L R Q



7 W : Company's trademark

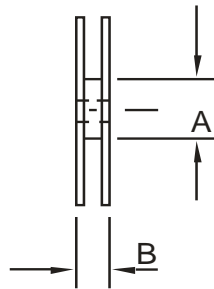
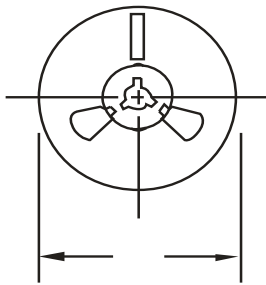
8 Product model : TSP10L120D For TSP10L120D-S

9 PDC information Æ

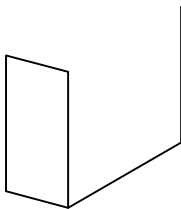


3 D F N D J L Q J , Q I R U P D W L R Q

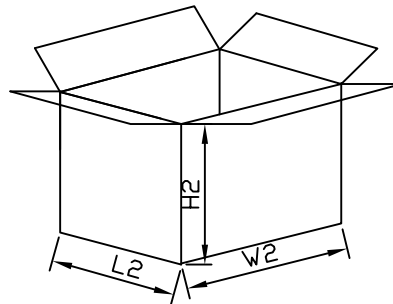
1.Reel Dimensions



2.Inside Box



3.Outside Box



3 D F N D J L Q J , Q I R U P D W L R Q